



### Features:

- RoHS Compliant
- 100 Watts
- DC 4.0 GHz
- AIN Ceramic
- Non-Nichrome Resistive
  Element
- Low VSWR
- 100% Tested
- Small Size

## **Outline Drawing**

# **Description**

The B100NA20X4 is high performance Aluminum Nitride (AIN) chip attenuator intended as a cost competitive alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators, and for use in power monitoring. The termination is also RoHS compliant!

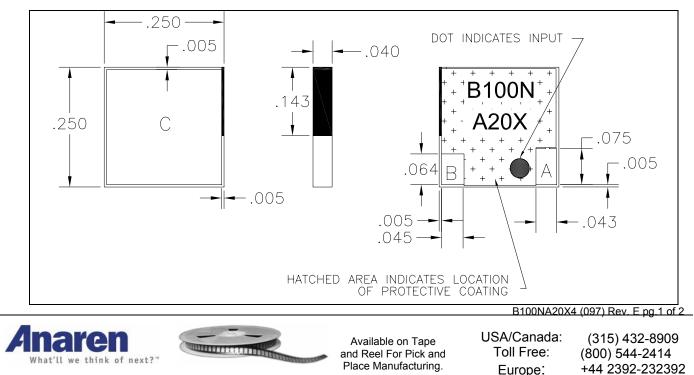
## **General Specifications**

Resistive Element	Thick film		
Substrate	AIN Ceramic		
Terminal Finish	Matte Tin over Nickel Barrier		
Operating Temperature	-55 to +150°C (see de rating chart)		
Tolerance is ±0.010", unless otherwise specified. Designed to meet of exceed applicable portions of MIL-E-5400. <b>All dimensions in inches.</b>			

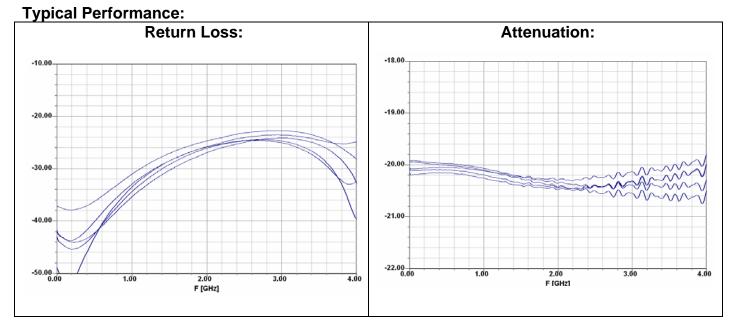
## **Electrical Specifications**

Attenuation Value:		20 dB, ± 1.0 dB, DC – 4.0 GHz		
Power:	100 '	100 Watts		
Frequency Range:		- 4.0 GHz		
Return Loss		>20 dB to 2.7 GHz		
	>19 dB to 4.0 GHz			
Value (A-B)	Value (A-C)	Value (B-C)	Tolerance	
81.8 Ω	50.9 Ω	50.9 Ω	± 4%	
Specification based on unit properly installed using suggested mounting instructions				

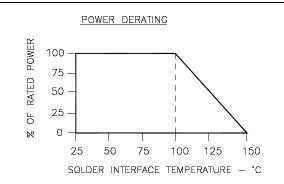
Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.** 



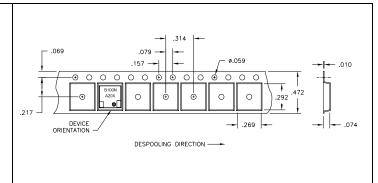




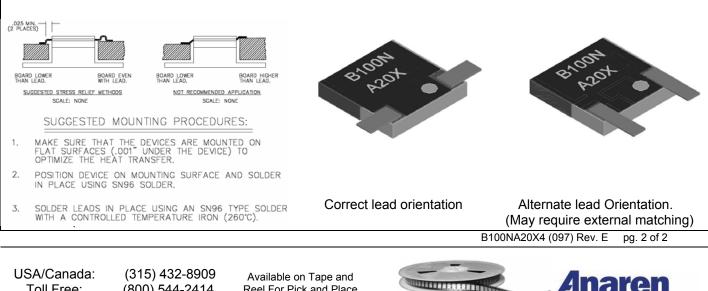
#### **Power De-rating:**



#### Tape & Reel:



#### **Mounting Footprint and Procedure:**



Toll Free: Europe:

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